

BBY58...

# **Silicon Tuning Diodes**

- Excellent linearity
- High Q hyperabrupt tuning diode
- Low series resistance
- Designed for low tuning voltage operation for VCO's in mobile communications equipment
- For low frequency control elements such as TCXOs and VCXOs
- Very low capacitance spread
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101



BBY58-05W

BBY58-02L/V BBY58-02W BBY58-03W

| 1 . | <u>⊢ N</u> | 2 |
|-----|------------|---|
|     |            |   |





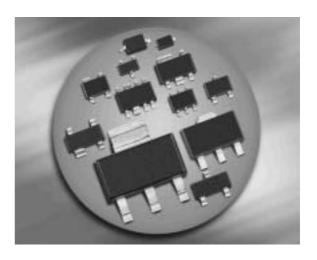
**BBY58-06W** 

| Туре      | Package  | Configuration    | <b>L<sub>S</sub></b> (nH) | Marking |  |
|-----------|----------|------------------|---------------------------|---------|--|
| BBY58-02L | TSLP-2-1 | single, leadless | 0.4                       | 88      |  |
| BBY58-02V | SC79     | single           | 0.6                       | 8       |  |
| BBY58-02W | SCD80    | single           | 0.6                       | 88      |  |
| BBY58-03W | SOD323   | single           | 0.6                       | 8 yel.  |  |
| BBY58-05W | SOT323   | common cathode   | 1.4                       | B5s     |  |
| BBY58-06W | SOT323   | common anode     | 1.4                       | B6s     |  |

## **Maximum Ratings** at $T_A = 25^{\circ}$ C, unless otherwise specified

| Parameter                   | Symbol           | Value   | Unit |
|-----------------------------|------------------|---------|------|
| Diode reverse voltage       | V <sub>R</sub>   | 10      | V    |
| Forward current             | / <sub>F</sub>   | 20      | mA   |
| Operating temperature range | T <sub>op</sub>  | -55 150 | °C   |
| Storage temperature         | T <sub>stg</sub> | -55 150 |      |

<sup>1</sup>Pb-containing package may be available upon special request





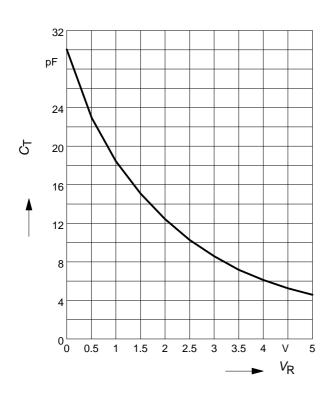
| Parameter   | Symbol          |      | Values |      |    |  |
|---|-----------------|------|--------|------|----|--|
|   |                 | min. | typ.   | max. | ]  |  |
| DC Characteristics  | ·               |      |        |      |    |  |
| Reverse current   | I <sub>R</sub>  |      |        |      | nA |  |
| $V_{R} = 8 \text{ V}$   |                 | -    | -      | 10   |    |  |
| $V_{\rm R} = 8 \text{ V}, \ T_{\rm A} = 85 \text{ °C}$                  |                 | -    | -      | 100  |    |  |
| AC Characteristics  |                 |      |        |      |    |  |
| Diode capacitance   | CT              |      |        |      | pF |  |
| $V_{R} = 1 V, f = 1 MHz$  |                 | 17.5 | 18.3   | 19.3 |    |  |
| $V_{R} = 2 V, f = 1 MHz$  |                 | 11.4 | 12.35  | 13.3 |    |  |
| $V_{R} = 3 V, f = 1 MHz$  |                 | 7.8  | 8.6    | 9.3  |    |  |
| $V_{R} = 4 V, f = 1 MHz$  |                 | 5.5  | 6      | 6.6  |    |  |
| $V_{\rm R} = 6  {\rm V},  f = 1  {\rm MHz}$                             |                 | 3.8  | 4.7    | 5.5  |    |  |
| Capacitance ratio   | $C_{T1}/C_{T3}$ | 1.9  | 2.15   | 2.4  | -  |  |
| $V_{\rm R} = 1  \text{V},  V_{\rm R} = 3  \text{V},  f = 1  \text{MHz}$ |                 |      |        |      |    |  |
| Capacitance ratio   | $C_{T1}/C_{T4}$ | 2.7  | 3.05   | 3.5  |    |  |
| $V_{\rm R} = 1  \text{V},  V_{\rm R} = 4  \text{V},  f = 1  \text{MHz}$ |                 |      |        |      |    |  |
| Capacitance ratio   | $C_{T4}/C_{T6}$ | 1.15 | 1.3    | 1.45 |    |  |
| $V_{\rm R} = 4 \text{ V}, V_{\rm R} = 6 \text{ V}, f = 1 \text{ MHz}$   |                 |      |        |      |    |  |
| Series resistance   | r <sub>S</sub>  |      |        |      | Ω  |  |
| <i>V</i> <sub>R</sub> = 1 V, <i>f</i> = 470 MHz, BBY58-02L, -07L4       |                 | -    | 0.3    | -    |    |  |
| $V_{R}$ = 1 V, f = 470 MHz, all other                                   |                 | -    | 0.25   | -    |    |  |

# **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

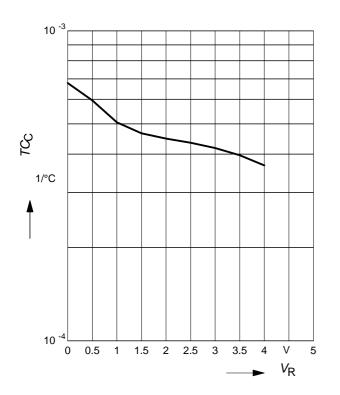


# **Diode capacitance** $C_{T} = f(V_{R})$

f = 1 MHz

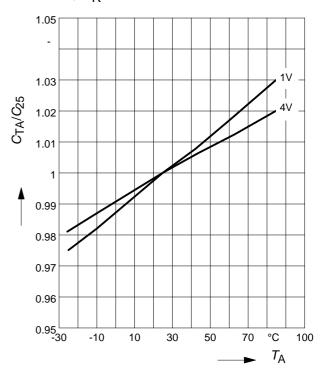


# Temperature coefficient of the diode capacitance $T_{CC} = f(V_R)$

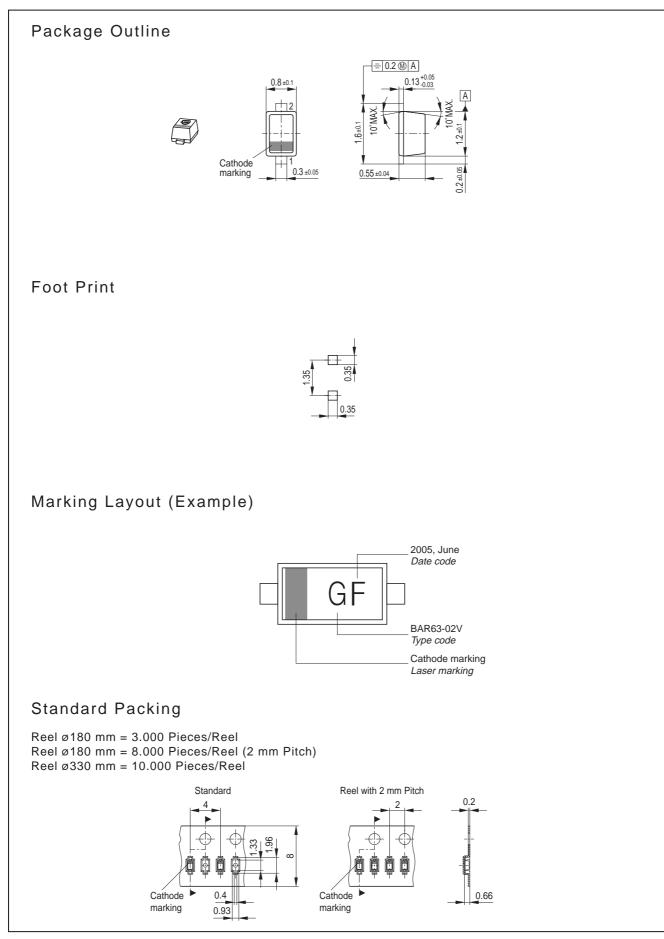


#### Normalized diode capacitance

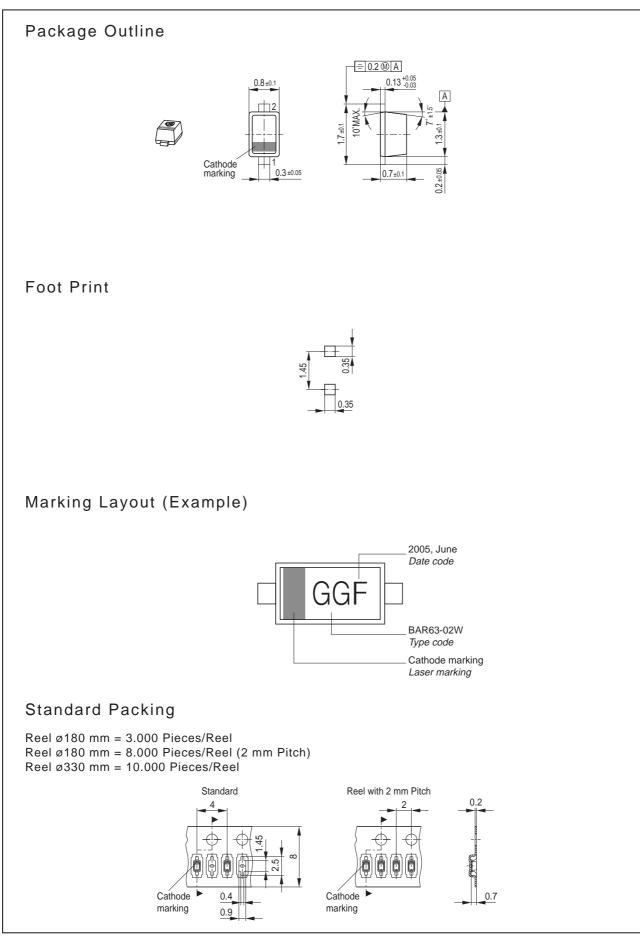
 $C_{(TA)}/C_{(25^{\circ}C)} = f(T_A)$ f = 1MHz, V<sub>R</sub> = Parameter











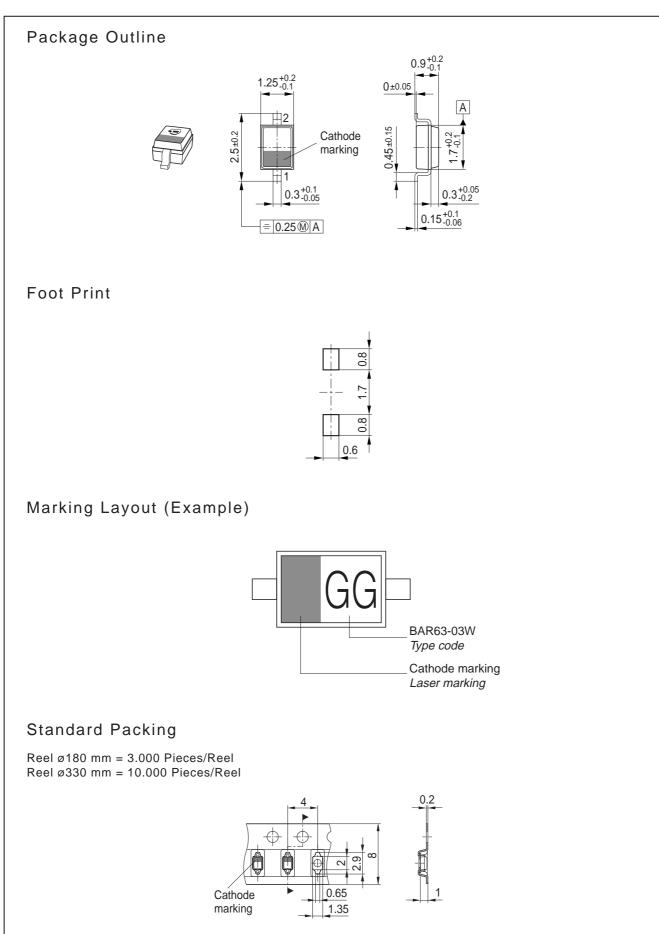


# Date Code marking for discrete packages with one digit (SCD80, SC79, SC75<sup>1)</sup>) CES-Code

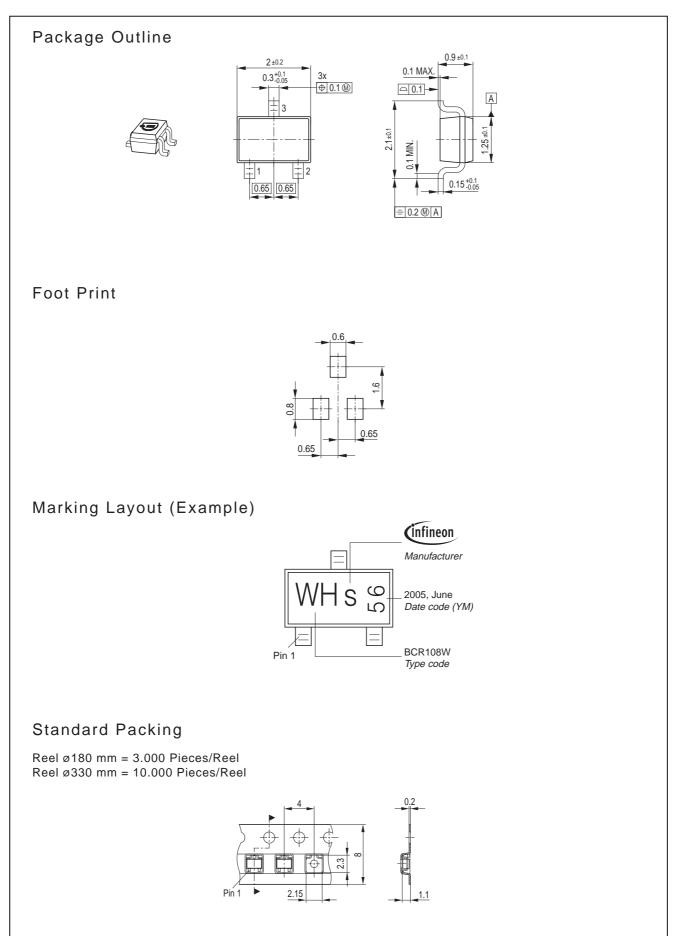
| Month | 2003 | 2004 | 2005 | 2006 | 2007 | 2008 | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 |
|-------|------|------|------|------|------|------|------|------|------|------|------|------|
| 01    | а    | р    | А    | Р    | а    | р    | А    | Р    | а    | р    | А    | Р    |
| 02    | b    | q    | В    | Q    | b    | q    | В    | Q    | b    | q    | В    | Q    |
| 03    | С    | r    | С    | R    | С    | r    | С    | R    | С    | r    | С    | R    |
| 04    | d    | S    | D    | S    | d    | S    | D    | S    | d    | S    | D    | S    |
| 05    | е    | t    | E    | Т    | е    | t    | Е    | Т    | е    | t    | Е    | Т    |
| 06    | f    | u    | F    | U    | f    | u    | F    | U    | f    | u    | F    | U    |
| 07    | g    | V    | G    | V    | g    | V    | G    | V    | g    | V    | G    | V    |
| 08    | h    | х    | Н    | Х    | h    | х    | Н    | Х    | h    | х    | Н    | Х    |
| 09    | j    | у    | J    | Y    | j    | у    | J    | Y    | j    | у    | J    | Y    |
| 10    | k    | Z    | K    | Z    | k    | Z    | K    | Z    | k    | Z    | K    | Z    |
| 11    | I    | 2    | L    | 4    | I    | 2    | L    | 4    | l    | 2    | L    | 4    |
| 12    | n    | 3    | Ν    | 5    | n    | 3    | Ν    | 5    | n    | 3    | Ν    | 5    |

1) New Marking Layout for SC75, implemented at October 2005.

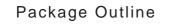


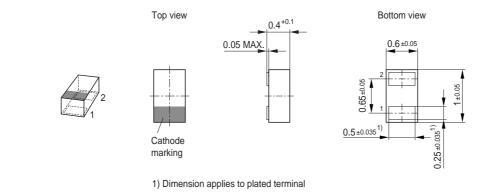






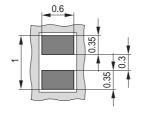




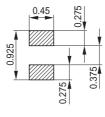


# Foot Print

For board assembly information please refer to Infineon website "Packages"

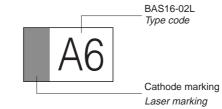


Copper Solder mask



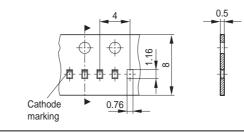
Stencil apertures

# Marking Layout (Example)



# Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel Reel ø330 mm = 50.000 Pieces/Reel (optional)





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